

isc Silicon NPN Power Transistor

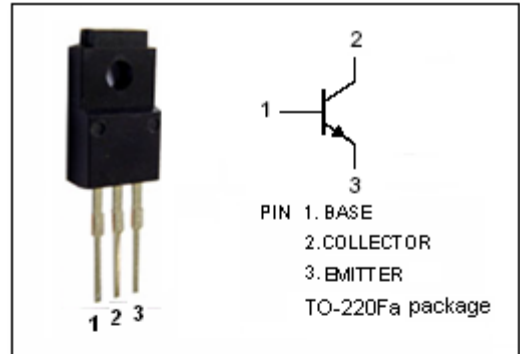
2SD1575

DESCRIPTION

- High Breakdown Voltage-
: $V_{CBO} = 1200V$ (Min)
- High Switching Speed
- High Reliability
- Wide Area of Safe Operation

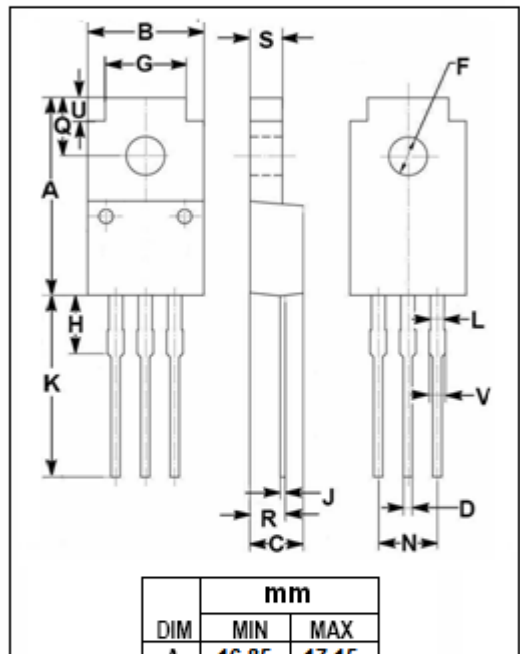
APPLICATIONS

- Designed for horizontal deflection output applications



ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	1200	V
V_{CES}	Collector-Emitter Voltage	1200	V
V_{CEO}	Collector-Emitter Voltage	700	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current- Continuous	2	A
I_{CP}	Collector Current-Peak	6	A
I_{BP}	Base Current-Peak	2.5	A
I_{BP}	Reverse Base Current-Peak	-1.5	A
P_C	Collector Power Dissipation @ $T_c=25^{\circ}C$	40	W
T_J	Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature Range	-55~150	$^{\circ}C$



DIM	mm	
	MIN	MAX
A	16.85	17.15
B	9.90	10.10
C	4.35	4.65
D	0.75	0.80
F	3.20	3.40
G	6.90	7.10
H	5.15	5.45
J	0.45	0.75
K	13.35	13.65
L	1.10	1.30
N	4.98	5.18
Q	4.85	5.15
R	2.95	3.25
S	2.70	2.90
U	1.75	2.05
V	1.30	1.50

isc Silicon NPN Power Transistor**2SD1575****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E=1\text{mA}; I_C=0$	6			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=2\text{A}; I_B=1\text{A}$			5.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=2\text{A}; I_B=1\text{A}$			1.5	V
I_{CBO}	Collector Cutoff Current	$V_{CB}=750\text{V}; I_E=0$			50	μA
		$V_{CB}=1200\text{V}; I_E=0$			1.0	mA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=6\text{V}; I_C=0$			50	μA
h_{FE}	DC Current Gain	$I_C=2\text{A}; V_{CE}=5\text{V}$	2			

Switching times

t_{stg}	Storage Time	$I_C=2.5\text{A}; I_{B1(end)}=1.1\text{A}; L_B=10\mu\text{H}$			9	μs
t_f	Fall Time				1.0	μs